

Title (en)  
ETCHING SOLUTION AND ETCHING METHOD

Title (de)  
ÄTZLÖSUNG UND ÄTZVERFAHREN

Title (fr)  
SOLUTION DE GRAVURE ET PROCÉDÉ DE GRAVURE

Publication  
**EP 2126967 A2 20091202 (DE)**

Application  
**EP 08706778 A 20080122**

Priority  
• DE 2008000099 W 20080122  
• DE 102007004060 A 20070122

Abstract (en)  
[origin: WO2008089733A2] The invention relates to an etching solution (1) comprising water, nitric acid, hydrofluoric acid, and sulphuric acid, containing 15 to 40% by weight of nitric acid, 10 to 41% by weight of sulphuric acid and 0.8 to 2.0% by weight of hydrofluoric acid. The invention also relates to the use of said etching solution for etching silicon and to etching methods for silicon wafers.

IPC 8 full level  
**H01L 21/306** (2006.01)

CPC (source: EP KR US)  
**C09K 3/1463** (2013.01 - EP US); **H01L 21/02087** (2013.01 - EP US); **H01L 21/0209** (2013.01 - EP US); **H01L 21/306** (2013.01 - KR); **H01L 21/30604** (2013.01 - EP US); **H01L 21/31111** (2013.01 - EP US)

Citation (search report)  
See references of WO 2008089733A2

Citation (examination)  
• US 2337062 A 19431221 - PAGE JR FRANKLIN H  
• EP 0496229 A2 19920729 - RIEDEL DE HAEN AG [DE]  
• WO 2005093788 A1 20051006 - RENA SONDERMASCHINEN GMBH [DE], et al

Designated contracting state (EPC)  
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MT NL NO PL PT RO SE SI SK TR

DOCDB simple family (publication)  
**DE 102007004060 A1 20080724**; **DE 102007004060 B4 20130321**; CN 101622697 A 20100106; EP 2126967 A2 20091202; KR 20090127129 A 20091209; US 2010120248 A1 20100513; WO 2008089733 A2 20080731; WO 2008089733 A3 20090108

DOCDB simple family (application)  
**DE 102007004060 A 20070122**; CN 200880002626 A 20080122; DE 2008000099 W 20080122; EP 08706778 A 20080122; KR 20097018377 A 20080122; US 52401608 A 20080122